EEL 6935: HW#3 REVISED

Due Friday, November 1, 2002 in class. Late homework loses $e^{\# \text{ of days late} - 1}$ percentage points. See the current late penalty at http://www.cnel.ufl.edu/hybrid/harris/latepoints.html

1. Solve for $I_{out}$ as a function of the difference of the two input voltages $(V_1 - V_2)$ for below threshold CMOS operation. As usual, first, assume $\kappa = 1$ and derive your answer. Then assume $\kappa$ is the same for all transistors but not equal to one and derive your answer. Simplify your expressions as much as possible. Show all of your work and explicitly state all assumptions, e.g. which transistors are in saturation, subthreshold operation, matching of devices, etc.

2. Solve for $I_{out}$ as a function of the difference of the two input voltages $(V_1 - V_2)$ for below threshold CMOS operation. As usual, first, assume $\kappa = 1$ and derive your answer. Then assume $\kappa$ is the same for all transistors but not equal to one and derive your answer. Simplify your expressions as much as possible. Show all of your work and explicitly state all assumptions, e.g. which transistors are in saturation, subthreshold operation, matching of devices, etc.

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3. Solve for $I_{out}$ as a function of $V_1$ and $V_2$ for the 5-transistor transamp in the \textbf{above-threshold} region. Develop a definition to quantify the width of the “linear region” of this curve. Come up with an approximate expression for the width of the linear region as a function of the above threshold bias voltage. What is the exact linear region width for the below threshold transamp according to your definition?

4. Explain the operation of the inner hair cell circuit in Fig. 1.9 of the cochlea paper by Sarpeshkar, Lyon and Mead. Could a simple inverter be used instead of transistors BA and PA to charge and discharge the capacitor $C_{HR}$? Explain why or why not.

5. Use a VLSI design system of your choice (e.g. CADENCE and layout a simple 5-transistor tranconductance amplifier in the 0.6μm AMI technology.). Make all of your transistors $6\lambda$ by $6\lambda$ except for current mirror transistors which should have a longer length of $20\lambda$. Make sure that you have well and substrate contacts. If possible, use software to verify that your layout is identical to a schematic or netlist that you create. You only need to turn in a plot of your layout.